



**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.3	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	50	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0		4.0	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 150V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 20A$		30	39	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 10V, I_D = 20A$		7		s

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	f = 1MHz	-	3400	-	pF
Output capacitance	$C_{oss}$		-	169	-	
Reverse transfer capacitance	$C_{rss}$		-	98	-	

**Gate Charge characteristics ( $T_a = 25^{\circ}C$ )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 25V$	-	57	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 8A$	-	12	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = 10V$	-			





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Fig.7 Switching Time

Fig.8 Gate Charge Waveform

